Abstracts

Bias-Dependent "Cold-(H)FET" Modeling

W. Stiebler, M. Matthes, G. Bock, T. Koppel and A. Schafer. "Bias-Dependent "Cold-(H)FET" Modeling." 1996 MTT-S International Microwave Symposium Digest 96.3 (1996 Vol. III [MWSYM]): 1313-1316.

A bias-dependent model for MESFET and HFET devices under zero drain bias pinched-off conditions is proposed. Parasitic capacitances are evaluated from bias-dependent Y parameters over the whole frequency range. For the first time, it is possible to clearly distinguish between all intrinsic and extrinsic capacitances by considering the distributed nature of the device.

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